

Silicon PNP Power Transistors

2SB707 2SB708

DESCRIPTION

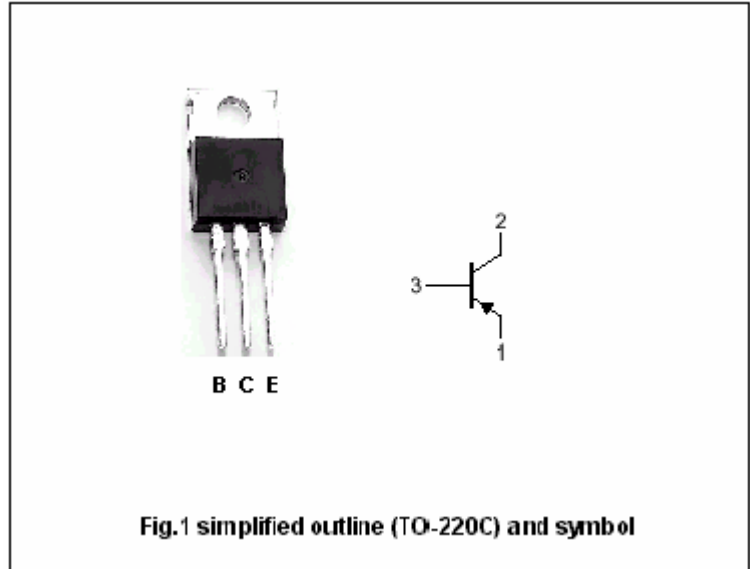
- With TO-220C package
- Complement to type 2SD568/569

APPLICATIONS

- For low frequency power amplifier
- low speed switching industrial use

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-80	V
V_{CEO}	Collector-emitter voltage	2SB707	-60	V
		2SB708	-80	
V_{EBO}	Emitter-base voltage	Open collector	-7	V
I_C	Collector current		-7	A
I_{CM}	Collector current-peak		-15	A
I_B	Base current		-3.5	A
P_C	Collector power dissipation	$T_a=25^\circ\text{C}$	1.5	W
		$T_C=25^\circ\text{C}$	40	
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-10mA; I _B =0	-60			V
			-80			
V _{CEsat}	Collector-emitter saturation voltage	I _C =-5A; I _B =-0.5 A			-0.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-5A; I _B =-0.5 A			-1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =-60V; I _E =0			-10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-10	μA
h _{FE-1}	DC current gain	I _C =-3A ; V _{CE} =-1V	40		200	
h _{FE-2}	DC current gain	I _C =-5A ; V _{CE} =-1V	20			

◆ h_{FE-2} classifications

R	O	Y
40-80	60-120	100-200

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PACKAGE OUTLINE



Fig.2 Outline dimensions (unindicated tolerance: ± 0.10 mm)